

MOSFET 100W, HF-1GHz

Manufacturers	NXP Semiconductor
Package/Case	SOT467
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for BLF871 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

BLF871 is a high-power LDMOS (Laterally Diffused Metal-Oxide Semiconductor) transistor manufactured by NXP Semiconductors. It is designed for use in a wide range of RF power amplifier applications, including those in the broadcast, industrial, scientific, and medical industries.

Features

High power output: The BLF871 is capable of delivering up to 700 watts of output power.

High efficiency: The device's high efficiency results in reduced power consumption and lower operating temperatures.

Broadband operation: The transistor can operate over a wide frequency range, from 470 MHz to 860 MHz.

High gain: The BLF871 has a high gain of 23 dB, making it ideal for use in high-power amplifier designs.

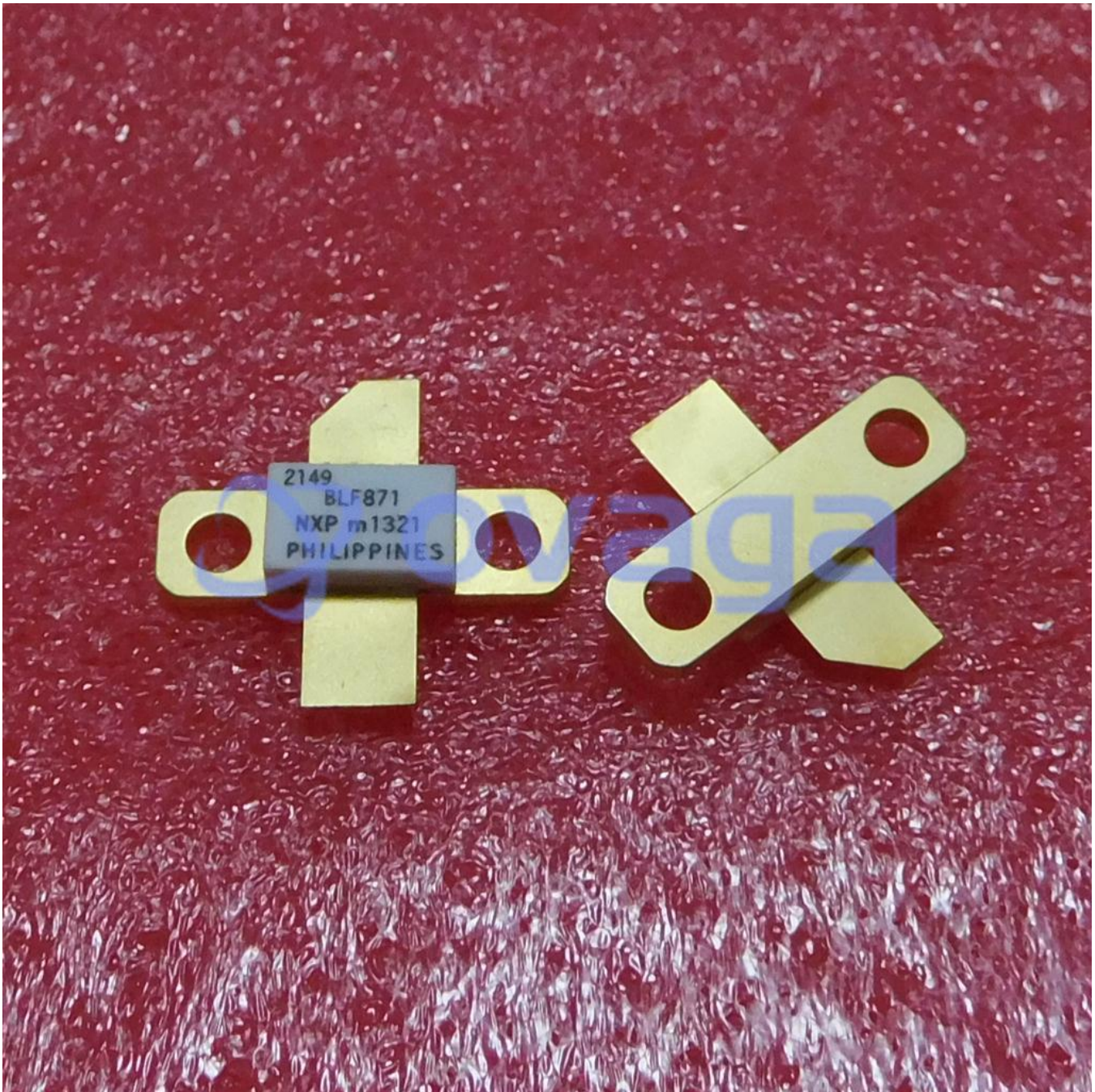
Application

Broadcast transmitters: The transistor is used in FM and TV broadcast transmitters.

Industrial heating and drying systems: The device is used in industrial RF heating and drying systems.

Medical and scientific equipment: The BLF871 is used in medical and scientific equipment that requires high-power RF amplification.





Related Products



[BLT50](#)

NXP Semiconductor
SOT-223



[BLF574](#)

NXP Semiconductor
TO-59



[BLF278](#)

NXP Semiconductor
SOT-262



[BLF245](#)

NXP Semiconductor
SOT-123A



BLF642

NXP Semiconductor
SOT467C



BLF248

NXP Semiconductor
SOT-262 A1



BLF175

NXP Semiconductor
TO-59



BLF878

NXP Semiconductor
SOT502B